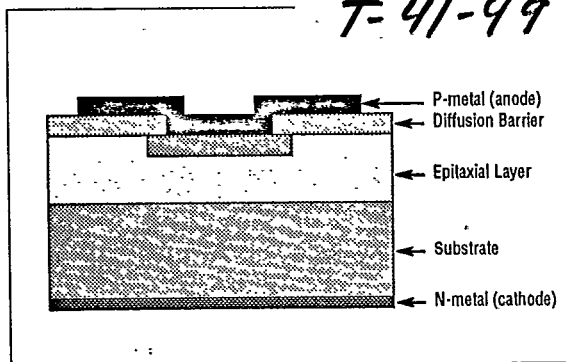
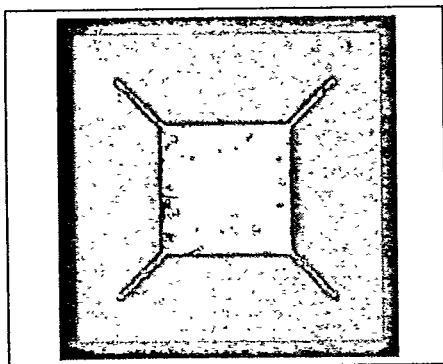


SIEMENS**RP-12C
Mask-Diffused GaAsP LED**

PART NO. 2680-7075

Custom
Optoelectronic
Products**DESCRIPTION**

Siemens RP-12C is a mask-diffused GaAsP light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for lamp and display applications.

MATERIAL

Epitaxial Layer: $\text{GaAs}_{1-x}\text{P}_x$: Te
 Substrate: GaAs : Si or GaAs : Te
 Metalizations: Anode Aluminum
 Cathode Gold-Germanium

Dimensions
 (center to center): Height 0.012"
 Width 0.012"
 Thickness 0.010"

TYPICAL DEVICE PARAMETERS

Forward I-V Characteristics	V_{F3}	1.70 V	@ 20 mA
	V_{F2}	1.64 V	@ 10 mA
	V_{F1}	1.45 V	@ 100 μA
Reverse I-V Characteristics	V_{R1}	-25.0 V	@ -10 μA
Peak EL Wavelength	λ	655 nm	@ 20 mA
Spectral Half-Width	FWHM	40 nm	@ 20 mA
Luminous Intensity	LI	500 μCd	@ 10 mA